





# Curling-PCM: Application-Specific Wear Leveling for Phase Change Memory based Embedded Systems

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#### Outline



- Introduction
  - Phase Change Memory (PCM)
  - PCM-based Embedded Systems
- Curling-PCM: Application-specific wear-leveling
  - Full-Curling
  - Partial-Curling
- Evaluation
- Conclusion

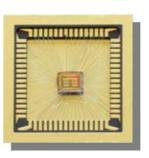
# **PCM (Phase Change Memory)**



- Why PCM (Phase Change Memory)?
  - Non-volatile, high density, low standby power...
  - Better than NOR/NAND flash in almost all metrics
  - Performance close to DRAM but with better scalability
  - NOR/DRAM replacement: PCM chips have been shipped by Micron (128Mb SPI/P8P; 1Gb LPDDR).



Samsung's PCM

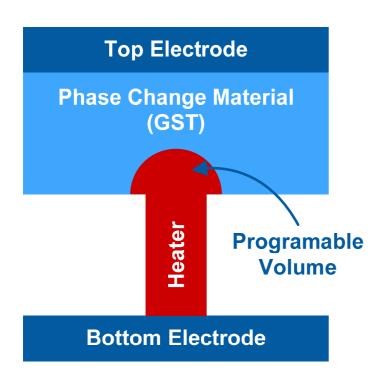


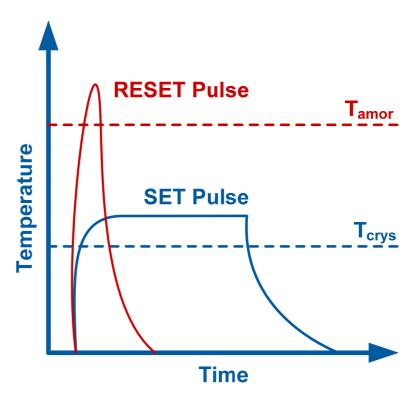
IBM's PCM

#### **How PCM works?**



■ Two states: amorphous (0) ← crystalline (1)



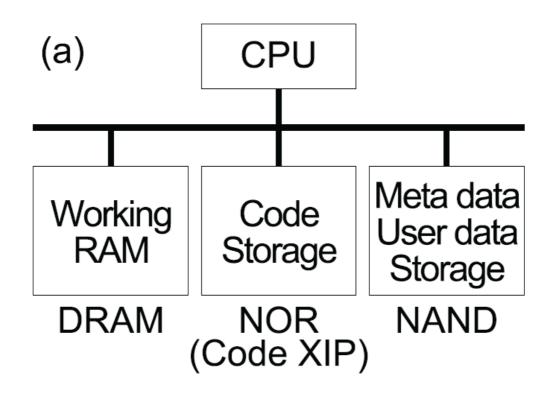


# Comparison of DRAM, PCM and NAND

■ PCM has limited endurance (10<sup>6</sup>~10<sup>8</sup> writes – DRAM: 10<sup>16</sup>)

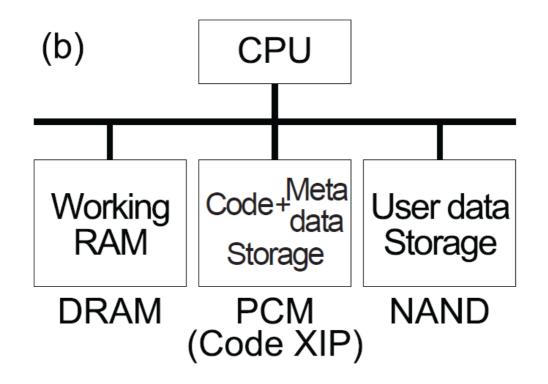
	DRAM	PCM	NAND
Non-Volatile	No	Yes	Yes
<b>Erase Unit</b>	Bit	Bit	Block
Power	~W/GB	100- 500mW/die	~100mW/die
Write Latency	<10ns	50-120ns	~100us
Write Voltage	2.5V	15V	<b>3V</b>
Read Latency	<b>50ns</b>	<b>50-100ns</b>	10-25us
Read Voltage	1.8v	<3V	<b>2V</b>
Endurance	<b>&gt;10</b> <sup>16</sup>	10 <sup>6</sup> -10 <sup>8</sup>	10 <sup>4</sup> -10 <sup>5</sup>
Retention	64ms	>10 years	>10 years

#### **Current Embedded Storage Architecture**



DRAM + NOR flash + NAND flash

### **PCM-based Embedded Systems**



The embedded storage architecture by utilizing PCM as NOR flash replacement with the exploration of its extra space

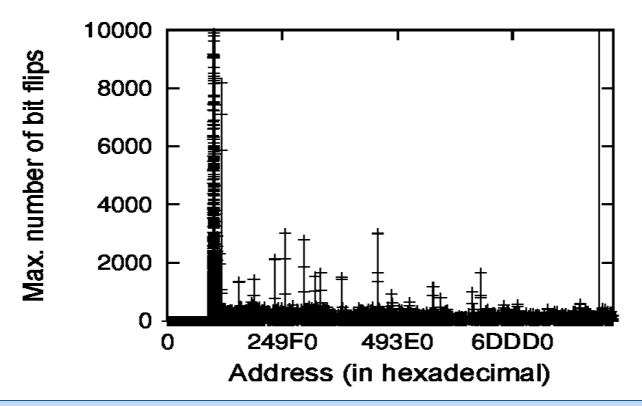
#### The Previous Work

- PCM management has been intensively studied in the general-purpose computing field.
  - Start-Gap [MICRO09], Differential write [ISCA 09-Zhang], Security refreshing [ISCA09], PCM SSD[HotStorage11, HPCA10], etc.
- Embedded systems (application-oriented): limited resources to manage PCM.
  - Hybrid SPM with PCM/SRAM [DATE11], Data scheduling/recomputation [DAC10].
  - Reduce energy [DAC11]
  - PCM-FTL [RTSS11]

#### **Motivation**



Distribution of write activities with Start-Gap<sup>[1]</sup>



[1] M. K. Qureshi, J. Karidis, M. Franceschini, V. Srinivasan, L. Lastras, and B. Abali, "Enhancing lifetime and security of PCM-based main memory with start-gap wear leveling," in MICRO, 2009.

# **Curling-PCM**

 Curling-PCM: evenly distribute write activities by utilizing application-specific features.



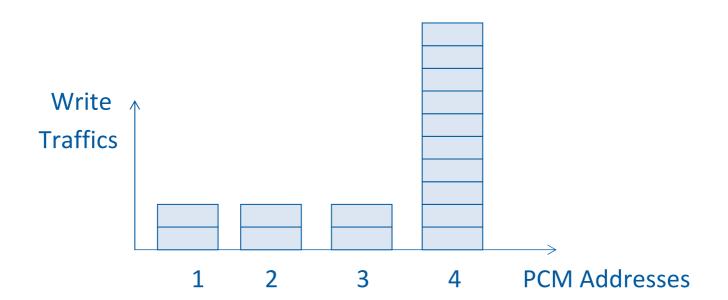
#### Basic idea:

- Identify hot areas by analyzing update frequencies of an application.
- Periodically move hot areas across PCM (threshold satisfied) so write traffics can be evenly distributed.

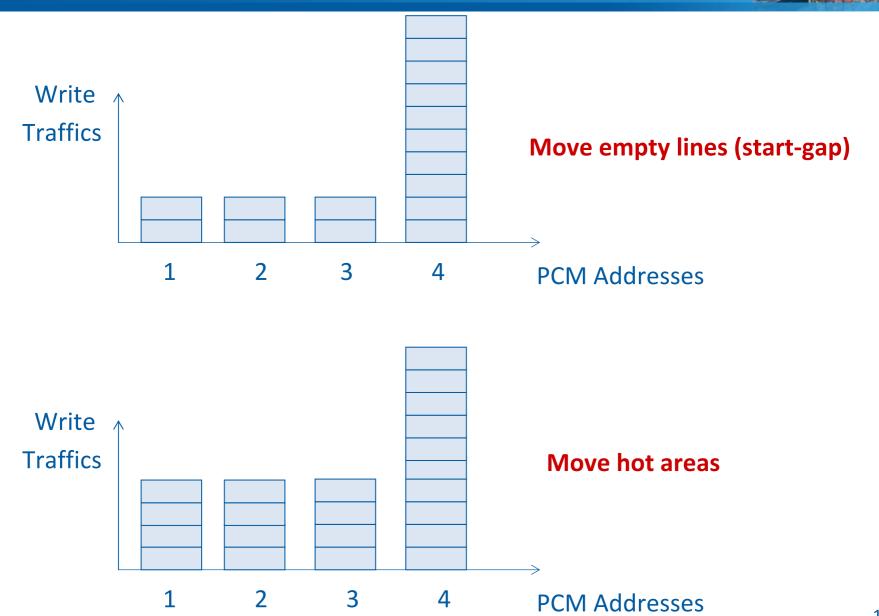
# Why moves hot areas not cold areas?

 Moving hot areas can more evenly distribute write traffics than moving cold areas.

#### **Original write distributions**



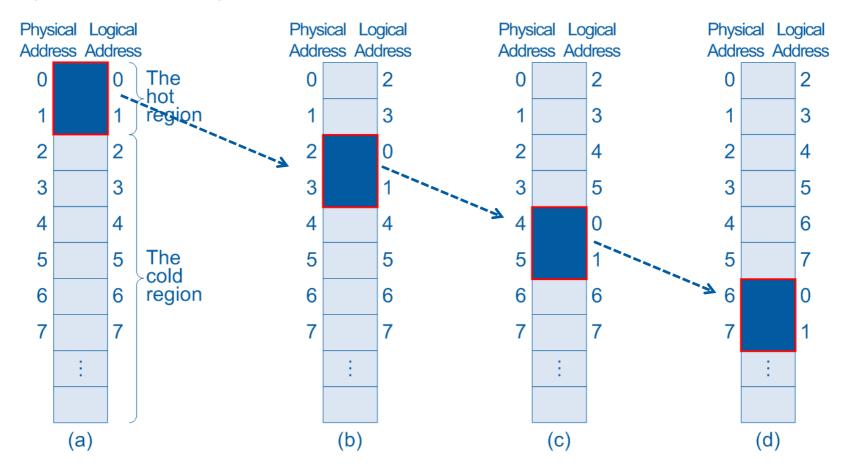
# Why moves hot areas not cold areas?



# **Full Curling**



 Group hot areas into a hot region and periodically move it



# **Full Curling Address Translation**

■ Three registers are needed to handle address translation.

$$PA = \begin{cases} (LA + R\_HStart) \bmod Len \\ & \text{if } LA \in hot \ region, \\ (LA + R\_HStart + Len - R\_CStartL) \bmod Len \\ & \text{if } LA < R\_CStartL, \\ (LA + R\_HStart + HLen - R\_CStartL) \bmod Len \\ & \text{if } LA \ge R\_CStartL. \end{cases}$$

PA: Physical address

LA: Logical address

**R\_HStart**: Current starting physical address of hot region

R\_CStartL: The first logical address following the hot region

Len: Total length of hot and cold regions

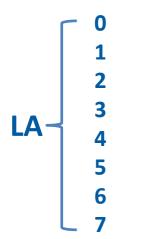
HLen: Length of hot region

# **Full Curling Mapping Example**



PA	LA	
0	0	
1	1	
2	2	1
3	3	
4	4	
5	5	
6	6	
7	7	
		D. HChaut.

R	_HStart:
R	<b>CStartL</b> :



1 <sup>st</sup>	$2^{nd}$	3rd	4 <sup>th</sup>	$5^{ m th}$	$6^{\mathrm{th}}$	$7^{\mathrm{th}}$
LA	LA	LA	LA	LA	LA	LA
2	2	2	0	4	4	4
3	3	3	1	5	5	5
0	4	4	4	0	6	6
1	5	5	5	1	7	7
4	0	6	6	6	0	2
5	1	7	7	7	1	3
6	6	0	2	2	2	0
7	7	1	3	3	3	1
2	4	6	0	2	4	6
4	6	2	4	6	2	4
PA	PA	PA	PA	PA	PA	PA
2	4	6	0	2	4	6
3	5	7	1	3	5	7
0						
	0	0	6	6	6	4
1	0 1	0 1	6 7	6 7	6 7	4 5
1 4						
	1	1	7	7	7	5
4	1 2	1 2	7 2	7 0	7 0	5 0

## **Partial Curling**

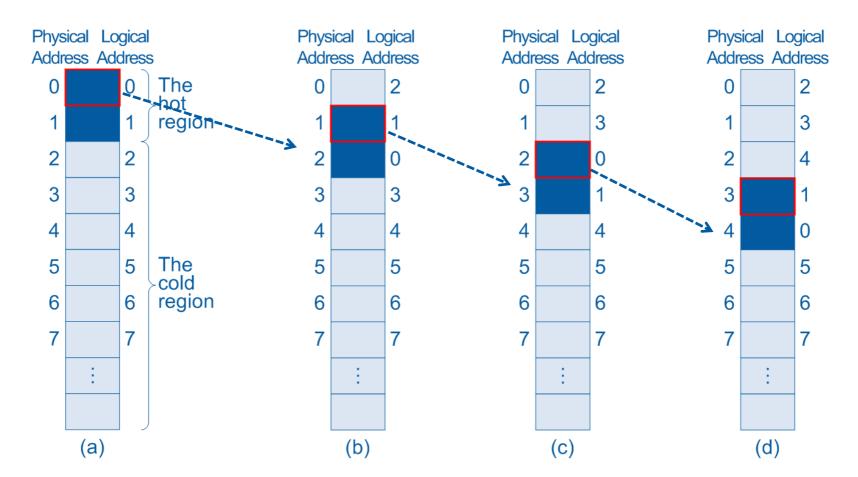


Full Curling moves all hot entries when handling a request, leading to *long* response time.

- Partial Curling
  - Divides hot region into smaller sub-regions
  - Move one sub-region following each request
  - Amortize overheads to multiple requests

# **Partial Curling**

 Divide the movement of hot region into small steps, and each step can be interleaved with the service of read/write requests.



## **Partial Curling**



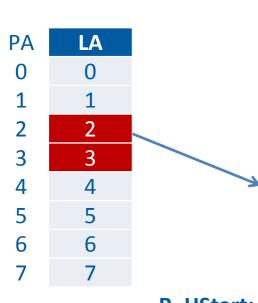
#### $\textbf{Algorithm III.1} \ Partial Curling Translate (LA)$

**Input:** LA - logical address of PCM entry

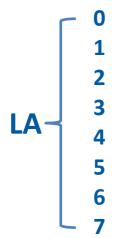
**Output:** PA - physical address of PCM entry

- 1: Let movedEntries = number of movedPCM entries so far.
- 2: Let prevOffset = previous starting hot region physical address.
- 3: Let newOffset = new starting hot region physical address.
- 4: Let  $hotRegion\_StartLA$  = starting logical address of hot region.
- 5: if  $LA \leq movedEntries + hotRegion\_StartLA$  then
- 6: // the entry has already been moved, use new parameters.
- 7: Obtain PA by conducting address translation according to translation equations with newOffset.
- 8: **else**
- 9: // the entry has not been moved, use the previous parameters.
- 10: Obtain PA by conducting address translation according to translation equations with prevOffset.
- 11: **end if**
- 12: **return** PA

# Partial Curling Mapping Example



$R_{\perp}$	<b>HStart:</b>



1 <sup>st</sup>	2 <sup>nd</sup>	3 <sup>rd</sup>	4 <sup>th</sup>	5 <sup>th</sup>	6 <sup>th</sup>	<b>7</b> <sup>th</sup>
LA						
0	0	0	0	2	2	4
1	1	1	1	1	3	3
4	4	4	4	4	4	2
3	5	5	5	5	5	5
2	2	6	6	6	6	6
5	3	3	7	7	7	7
6	6	2	2	0	0	0
7	7	7	3	3	1	1
4	6	0	2	4	6	0
PA						
0	0	0	0	6	6	6
1	1	1	1	1	7	7
4	4	6	6	0	0	2
3	5	5	7	7	1	1
2	2	2	2	2	2	0
5	3	3	3	3	3	3
6	6	4	4	4	4	4
7	7	7	5	5	5	5

#### **Evaluation**



 Applications – the extra space of PCM is used to manage NAND flash.

PCM is used to store the address mapping table of FTL in practice. This is used in our experiments.

 We compare three schemes: PCM-FTL, Start-Gap and our scheme—Curling-PCM.

#### **Evaluation**



#### PCM-FTL [RTSS-11]:

- A two-level mapping mechanism— the page-level mapping for infrequent updates, and a tiny buffer with block-level mapping for sequential updates.
- The tiny buffer becomes very hot.
- Start-Gap [Micro-09]
  - Employ an additional empty line as "gap" and move it periodically.
  - In our experiments, one line is 4 bytes, and the threshold is set to 100 writes (same as Micro-09 paper).

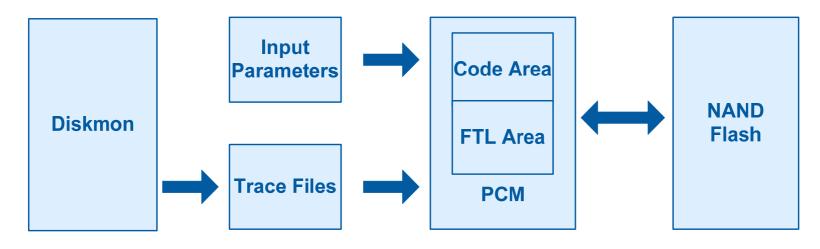
#### Curling-PCM:

- The tiny buffer and a few page table entries are hot so they are grouped as "the hot region".
- The hot region has 2000 lines, and the threshold is 20,000 writes.

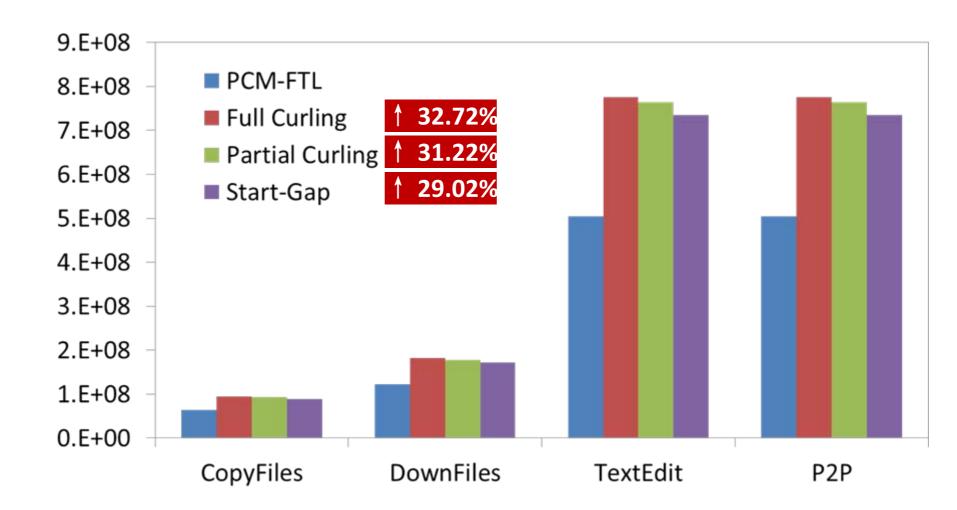
#### **Evaluation**



- Experimental Setup
  - Simulation Platform: Linux 2.6.29
    - PCM chip (32 Mb)
    - NAND flash memory (1GB)
- Traces:
  - CopyFiles, DownFiles, TextEdit, P2P
- Metrics:
  - Maximum & Total number of writes of PCM cells

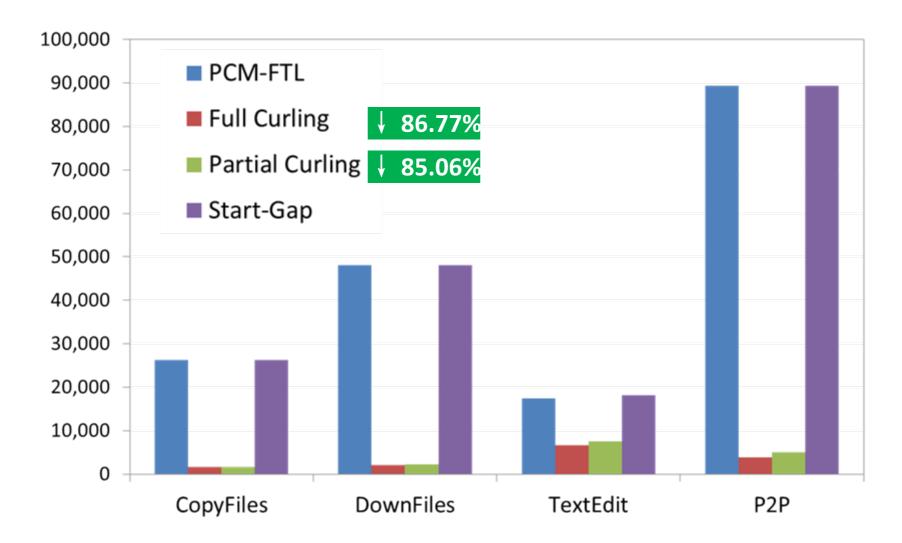






COMPARISON OF THE TOTAL NUMBER OF BIT FLIPS

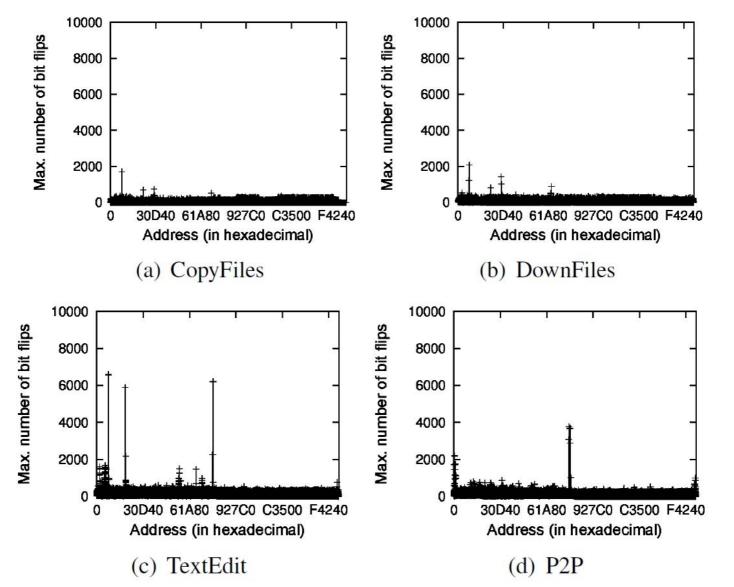




COMPARISON OF THE MAX NUMBER OF BIT FLIPS

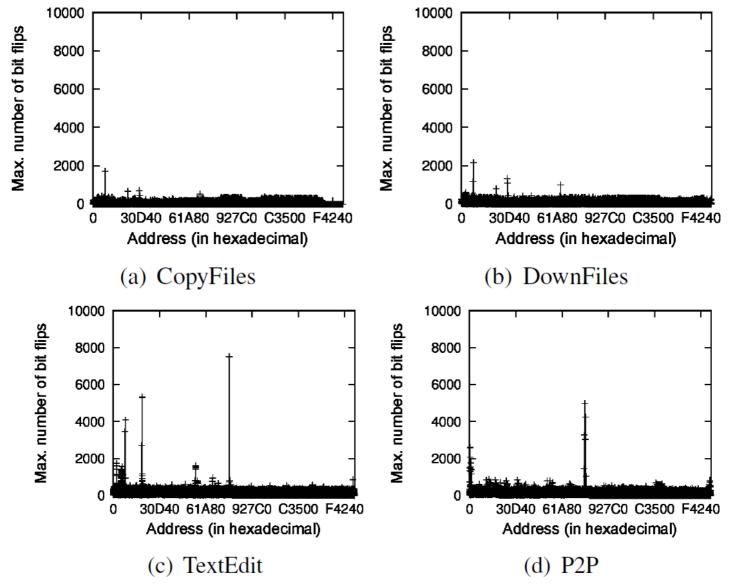


Distribution of the maximum number of bit flips by applying Curling-PCM with full curling





Distribution of the maximum number of bit flips by applying Curling-PCM with partial curling

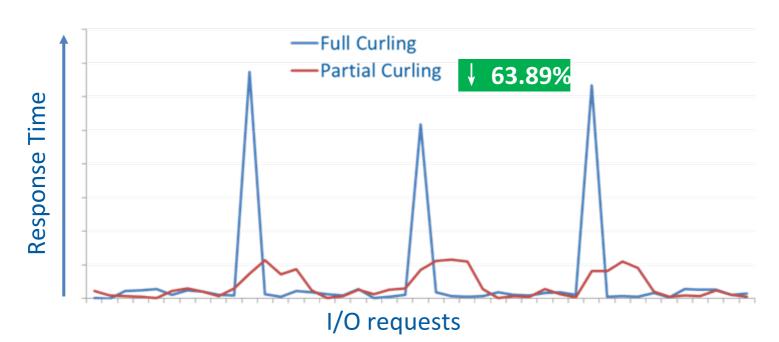




#### COMPARISON OF RESPONSE TIME VARIATION.

	Full Curling			Partial Curling			
Trace	Min (μs)	Max (μs)	Variation	Min (μs)	Max (μs)	Variation	Reduction over Full Curling
CopyFiles	0.13	2236.10	9380.94	0.13	961.80	2121.41	77.39%
DownFiles	0.05	3870.30	8140.94	0.05	1875.30	1866.43	77.07%
TextEdit	0.38	3160.80	9169.41	0.38	1729.20	2366.22	74.19%
P2P	0.18	18282.25	15249.94	0.18	16287.25	11145.33	26.92%
Average	0.18	6887.36	10485.31	0.18	5213.39	4374.85	63.89%

Variation = 
$$\frac{1}{Total\ Num\ Req} \times \sum_{i=1}^{Total\ Num\ Req} [T_i - \bar{T}]^2$$



#### Conclusion



We have proposed an application-specific wear leveling technique, called Curling-PCM, to evenly distribute write activities across the PCM chip for better endurance.

Experimental results show that Curling-PCM can effectively distribute write activities evenly and improve the lifetime of PCM chips compared to previous work.







